

30. The process according to claim 29, wherein said first insulating film is substantially formed of  $\text{SiO}_2$ , said second insulating film is substantially formed of  $\text{Si}_3\text{N}_4$ , and said third insulating film is substantially formed of  $\text{SiO}_2$ .

31. The process according to claim 30, wherein said metal wiring is formed of Al.

B  
and  
32. The process according to claim 29, further comprising the step of forming a barrier metal film on inner surfaces of said groove and said contact hole.

33. The process according to claim 32, wherein said barrier metal film is formed of Nb.

34. The process according to claim ~~32~~ <sup>31</sup>, wherein said metal wiring is formed of Cu.

35. The process according to claim 29, further comprising the step of forming a carbon film on said third insulating film.

36. The process according to claim ~~28~~ <sup>35</sup>, further comprising the step of forming a barrier metal film on inner surfaces of said groove.

37. The process according to claim 36, wherein said barrier metal film is formed of Nb.

38. The process according to claim 35, further comprising the step of forming another barrier metal film on said metal wiring.

39. The process according to claim 38, wherein said another barrier metal film is formed of Nb.--

#### REMARKS

Favorable consideration of this application is respectfully requested. Claims 28-39 are now present in this application, the cancellation of claims 1-27 having been respectfully requested. New claims 29-39 have been added by way of the present amendment.